

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	13mΩ@10V	55A



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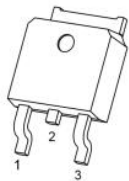
Feature

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery

Applications

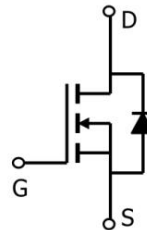
- Consumer electronic power supply
- Motor control Synchronous rectification
- Isolated DC/DC convertor
- Invertors

Package

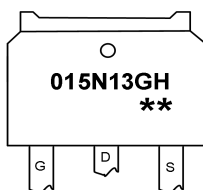


TO-252(1:G 2:D 3:S)

Circuit diagram



Marking



015N13GH : Product code
* : Month code

Order Information

Device	Package	Unite/Tape
SP015N13GHTH	SOT-23	2500

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	150	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾ , TC=25 °C	I_D	55	A
Pulsed drain current ²⁾ , TC=25 °C	I_{DM}	220	A
Power dissipation ³⁾ , TC=25 °C	P_D	142	W
Single pulsed avalanche energy ⁴⁾	E_{AS}	424	mJ
Thermal resistance, junction-case	$R_{\theta JC}$	0.88	°C/W
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

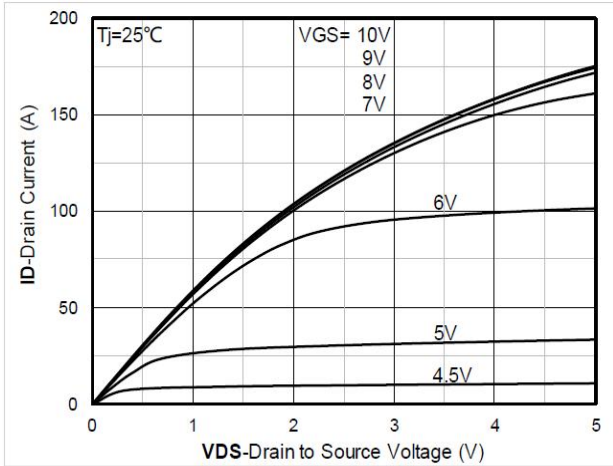
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$	150			V
Drain-source leakage current	I_{DSS}	$V_{DS}=150\text{ V}, V_{GS}=0\text{ V}$			1	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 20\text{ V}$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$	2	3	4	V
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=20\text{ A}$		13	16	$\text{m}\Omega$
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=75\text{ V}, f=1\text{ MHz}$		2230		pF
Output capacitance	C_{oss}			293		pF
Reverse transfer capacitance	C_{rss}			22		pF
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{GS}=10\text{ V}, V_{DS}=75\text{ V}, R_G=2.5\Omega, I_D=2\text{ A}$		16		ns
Rise time	t_r			42		ns
Turn-off delay time	$t_{d(off)}$			24		ns
Fall time	t_f			4.8		ns
Total gate charge	Q_g	$I_D=30\text{ A}, V_{DS}=75\text{ V}, V_{GS}=10\text{ V}$		37		nC
Gate-source charge	Q_{gs}			10.2		nC
Gate-drain charge	Q_{gd}			16.8		nC
Drain-Source Diode Characteristics						
Diode forward voltage	V_{SD}	$I_S=1\text{ A}, V_{GS}=0\text{ V}$			1.2	V
Reverse recovery time	t_{rr}	$I_S=12\text{ A}, di/dt=100\text{ A}/\mu\text{s}$		89		ns
Reverse recovery charge	Q_{rr}			279		nC
Peak reverse recovery current	I_{rrm}			6.4		A

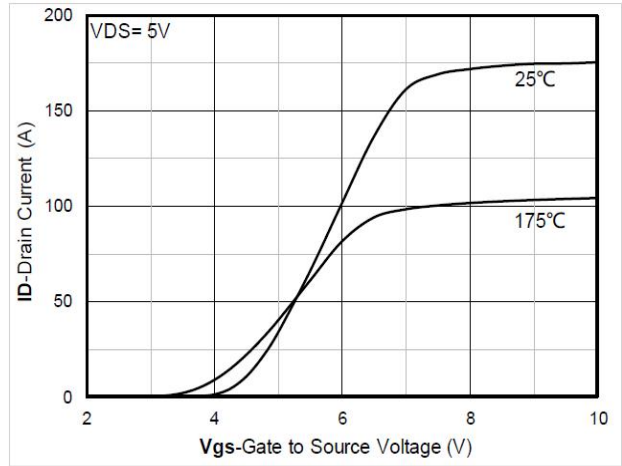
Notes:

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=50\text{ V}, V_G=10\text{ V}, R_G=25\Omega, L=0.5\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

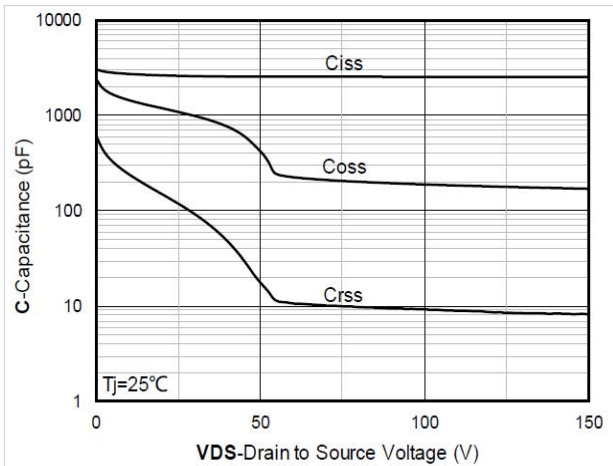
Typical Characteristics



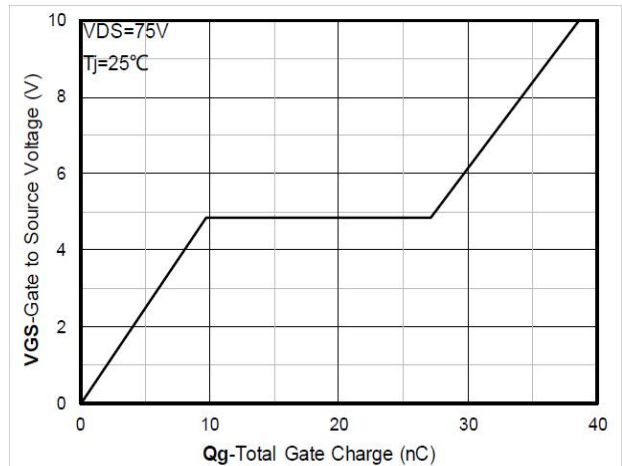
Output Characteristics



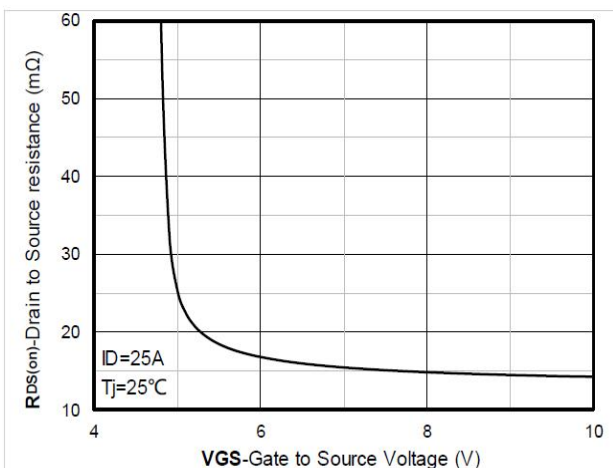
Transfer Characteristics



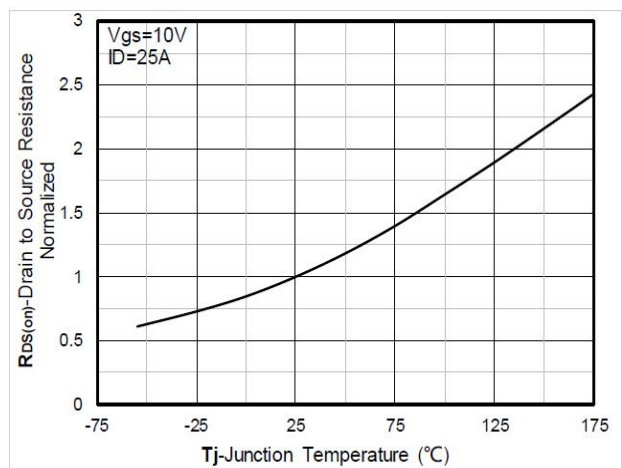
Capacitance Characteristics



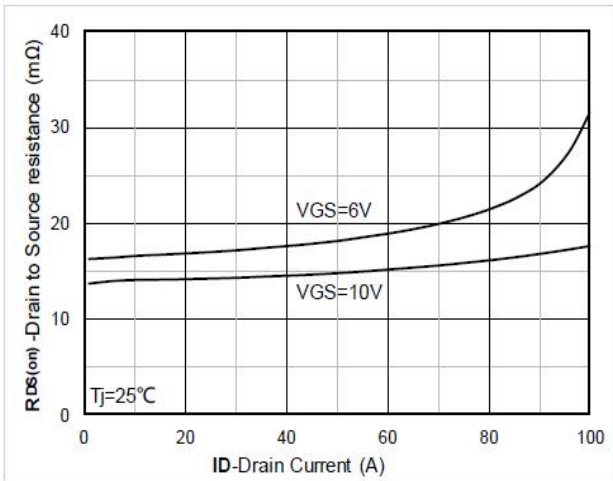
Gate Charge



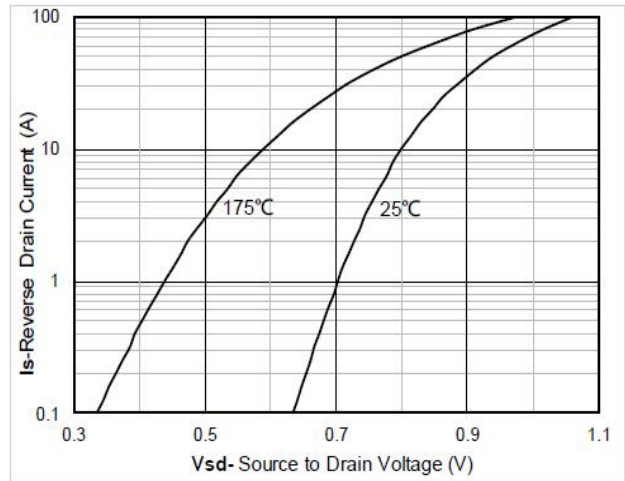
On-Resistance vs Gate to Source Voltage



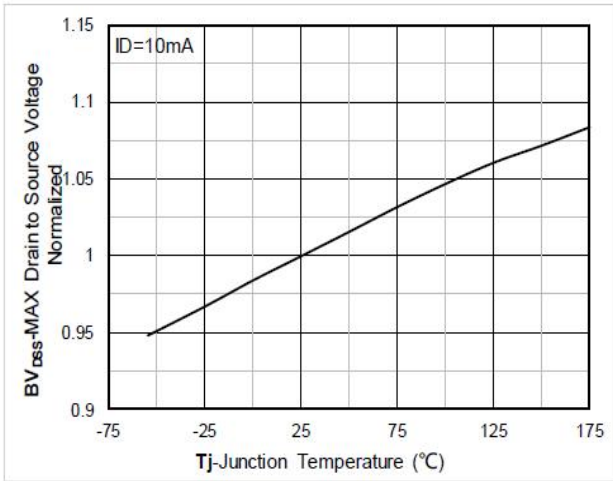
Normalized On-Resistance



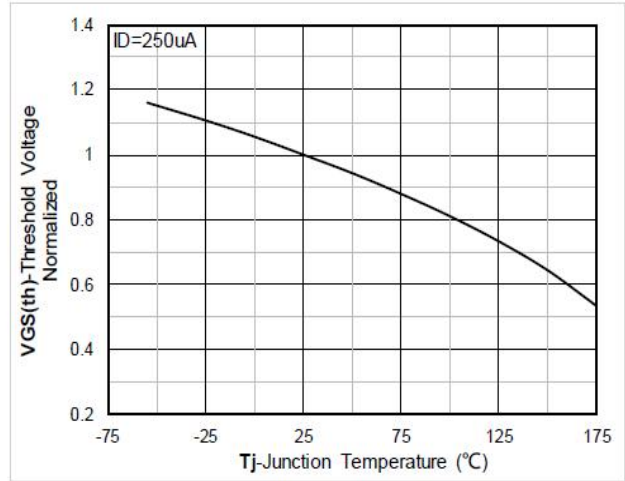
RDS(on) VS Drain Current



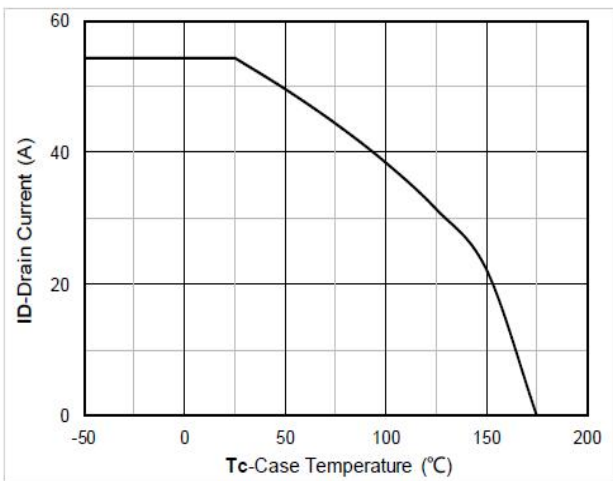
Forward characteristics of reverse diode



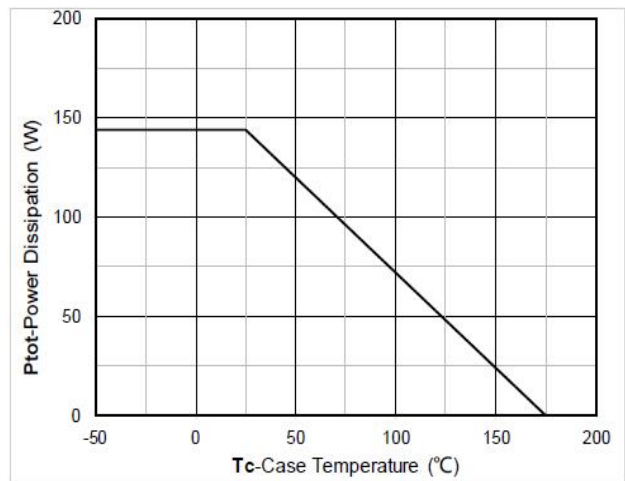
Normalized breakdown voltage



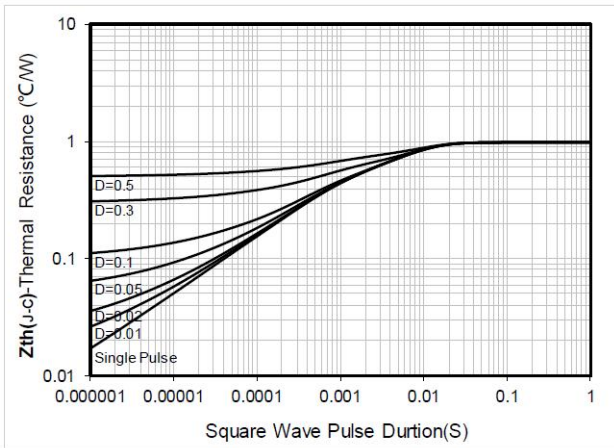
Normalized Threshold voltage



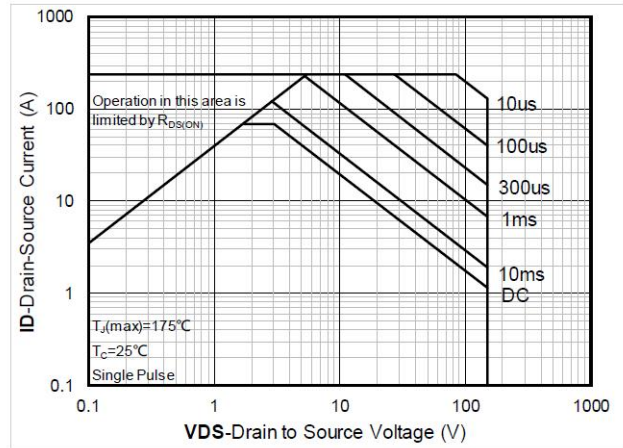
Current dissipation



Power dissipation



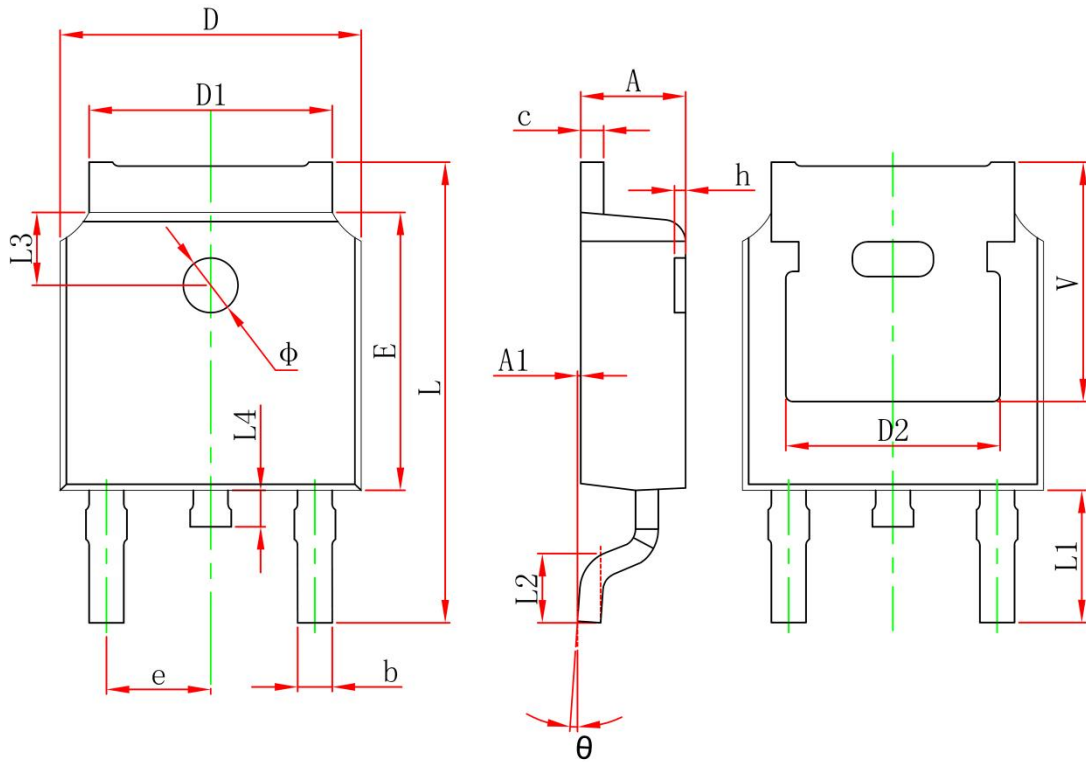
Maximum Transient Thermal Impedance



Safe Operation Area



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	

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